Abstracts

Properties of FET Parameter Statistical Data Bases

J. Purviance, M. Meehan and D. Collins. "Properties of FET Parameter Statistical Data Bases." 1990 MTT-S International Microwave Symposium Digest 90.1 (1990 Vol. I [MWSYM]): 567-570.

Statistical data bases are often used to characterize the statistics of a FET. This paper shows that a data base containing FET model parameter marginal probability density functions and covariance matrix is not sufficient to describe the FET's S-parameter statistics. This result is important to those developing statistical data bases for GaAs FETs. The implications of this work to simulation and CAD are discussed and a solution to this problem, the Truth Model, is presented.

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